PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Allen et al.

Serial No.: To Be Assigned Filed: Concurrently Herewith

METHODS OF FABRICATING SILICON CARBIDE METAL-SEMICONDUCTOR

FIELD EFFECT TRANSISTORS

Date: November 12, 2003

Mail Stop PATENT APPLICATION Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

Attached is a list of documents on form PTO-1449. Items 1-56 listed on the PTO-1449 were cited in parent application Serial No. 09/567,717, filed May 10, 2000. Since the benefit of this application is claimed under 35 U.S.C. §120, no copies need to be furnished in accordance with 37 C.F.R. §1.98(d); however, copies will be furnished on request. It is requested that these documents be considered by the Examiner and officially made of record in accordance with the provisions of 37 C.F.R. §1.56 and Section 609 of the MPEP.

No fee is believed due. However, the Commissioner is hereby authorized to charge any deficiency or credit any overpayment to Deposit Account No. 50-0220.

Respectfully submitted,

Elizabeth A. Stanek Registration No. 48,568

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CATION, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450

Attorney Docket Number: Serial No.: FORM PTO-1449 U.S. Department of Commerce Patent and Trademark Office 5308-127DV **TBA** LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary) Applicants: Allen, et al. Filing Date: Concurrently Herewith Group: **U. S. PATENT DOCUMENTS** Examiner Document Filing Date Initial Number Date Name Class Subclass if Appropriate 1. US2003/0075719 04/2003 257 77 Sriram 2. 6,316,793 11/2001 Sheppard et al. 257 103 77 3. 6,218,680 04/2002 Carter, Jr. et al. 257 77 4. 6,121,633 09/2000 Singh et al. 257 5. 6,107,649 08/2000 Zhao 257 138 770 6. 5,972,801 10/26/99 Lipkin, et al 438 77 7. 5,925,895 07/20/99 Sriram, et al. 257 8. 5,900,648 05/04/99 Harris et al. 257 77 9. 5,895,939 4/20/99 Ueno 254 279 19. 257 77 5,719,409 02/1998 Singh et al. 11. 5,686,737 11/1997 Allen 257 77 Agarwaa et al. 257 12. 5,510,630 04/1996 77 3/21/95 257 57 13. 5,399,883 Baliga 77 257 14. 5,396,085 03/07/95 Baliga 15. 04/20/93 Suzuki et al. 257 77 5,229,625 257 77 16. 5,270,554 12/14/93 **Palmour** 77 257 17. 5,264,713 11/1993 **Palmour** 08/07/90 357 13 18. 4,947,218 Edmond, et al. 71 19. 4,897,710 01/30/90 Suzuki et al 357

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